



High Power next Core (HPnC)

FEATURES

- **Latest chip technology (X-series and SiC-SBD)**
 - ▶ Available with Fuji X-series IGBT and FWD
 - ▶ Also available with Fuji SiC FWD
- **High reliability**
 - ▶ CTI>600 for higher anti-tracking
 - ▶ High thermal cycling capability with ultrasonic welded terminals and MgSiC base plate
 - ▶ Improvement of delta Tj power cycle capability by using 7G Package technology
 - ▶ Tj operation target is 175 °C
- **RoHS compliance**
 - ▶ RoHS solder
 - ▶ Ultrasonic welded terminals
- **Over temperature protection**
 - ▶ Thermal sensor installed

Line-up Plan

	Technology	Rated Voltage	Chip IGBT / FWD
	Silicon	1700 V	1000 A
	(IGBT/Si-Diode)	3300 V	450 A
	Hybrid	1700 V	1000 A
	(IGBT/SiC-SBD)	3300 V	450 A